

Silicon NPN Power Transistors

2SC5129

DESCRIPTION

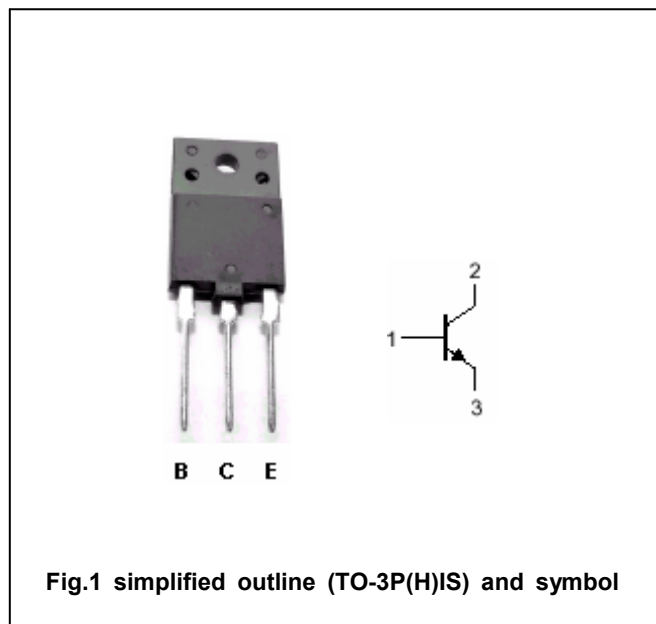
- With TO-3P(H)IS package
- High speed
- High voltage
- Low saturation voltage

APPLICATIONS

- Horizontal deflection output for high resolution display,colorTV
- High speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
I_{CM}	Collector current-Peak		20	A
I_B	Base current		5	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	600			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A ; I_B=1.5A$			3.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A ; I_B=1.5A$			1.4	V
I_{CBO}	Collector cut-off current	$V_{CB}=1500V ; I_E=0$			1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	10		30	
h_{FE-2}	DC current gain	$I_C=6A ; V_{CE}=5V$	4		8	
C_{ob}	Collector output capacitance	$I_E=0 ; V_{CB}=10V, f=1MHz$		135		pF
f_T	Transition frequency	$I_C=0.1A ; V_{CE}=10V$		1.7		MHz

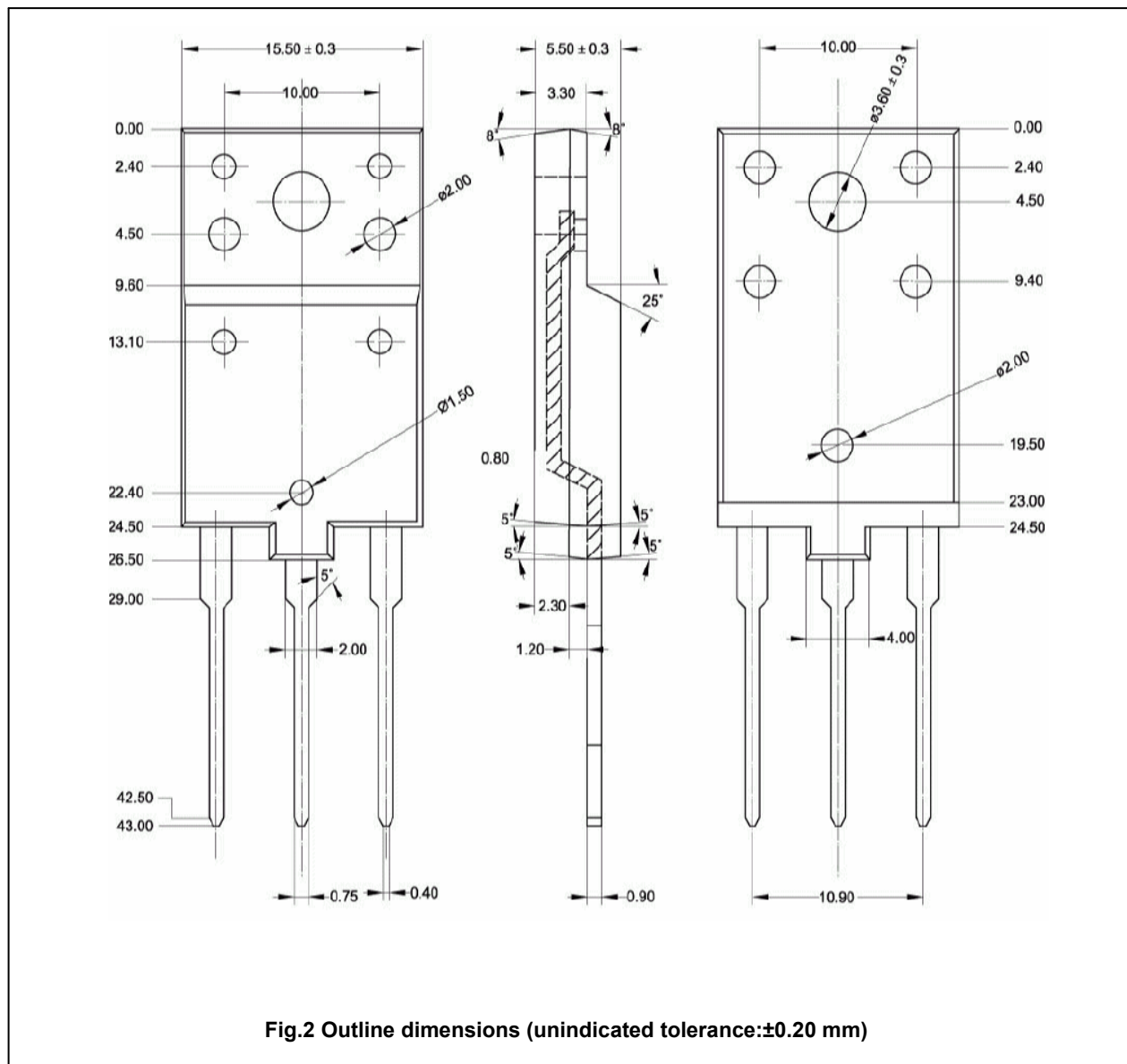
Switching times (inductive load)

t_s	Storage time	$I_{CP}=5A ; I_{B1(end)}=1A$ $f_H=64kHz$			4.0	μs
t_f	Fall time				0.3	μs

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PACKAGE OUTLINE



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